# BLF578XR; BLF578XRS

### **Power LDMOS transistor**

Rev. 1 — 30 January 2012

Objective data sheet

### 1. Product profile

### 1.1 General description

A 1400 W extremely rugged LDMOS power transistor for broadcast and industrial applications in the HF to 500 MHz band. This product is an enhanced version of the BLF578 using NXP's XR process to provide maximum ruggedness capability in the most severe applications without compromising the RF performance.

Table 1. Application information

Mode of operation	f	V <sub>DS</sub>	PL	Gp	η <sub>D</sub>
	(MHz)	(V)	(W)	(dB)	(%)
CW	108	50	1200	26	75
pulsed RF	225	50	1400	23	69

#### 1.2 Features and benefits

- Typical pulsed performance at frequency of 225 MHz, a supply voltage of 50 V and an  $I_{Dq}$  of 40 mA, a  $t_p$  of 100  $\mu$ s with  $\delta$  of 20 %:
  - ◆ Output power = 1400 W
  - Power gain = 23 dB
  - ◆ Efficiency = 69 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications



## 2. Pinning information

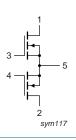
Table 2. Pinning

Description SOT539A)	Simplif	ied outline	Graphic symbol
-			
drain1		_	
drain2	1	2	1 . 🖵
gate1		5	
gate2	3	4	3 - 5
source	[1]		4
			' <u></u>
			2 sym117
	drain2 gate1 gate2	drain2 gate1 gate2	drain2 gate1 gate2  1 2 5 5

#### BLF578XRS (SOT539B)

1	drain1	
2	drain2	
3	gate1	
4	gate2	
5	source	<u>[1]</u>





[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

	•				
Type number	Package				
	Name	Description	Version		
BLF578XR	-	flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A		
BLF578XRS	-	earless flanged balanced LDMOST ceramic package; 4 leads	SOT539B		

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	110	V
$V_{GS}$	gate-source voltage		-6	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		-	225	°C

BLF578XR\_BLF578XRS

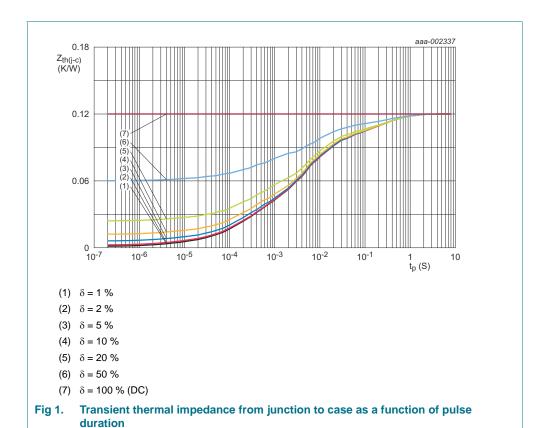
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### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	T <sub>j</sub> = 150 °C	[1][2] 0.12	K/W
$Z_{\text{th(j-c)}}$	transient thermal impedance from junction to case	$T_j$ = 150 °C; $t_p$ = 100 $\mu s$ ; $\delta$ = 20 %	<u>[3]</u> 0.035	K/W

- [1]  $T_j$  is the junction temperature.
- [2] Rth(j-c) is measured under RF conditions.
- [3] See Figure 1.



**Power LDMOS transistor** 

### 6. Characteristics

### 6.1 DC characteristics

Table 6. DC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

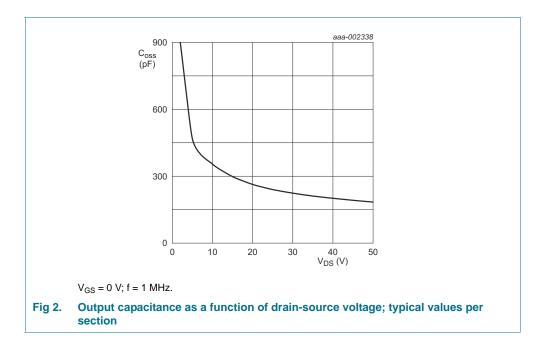
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.5 \text{ mA}$	110	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 500 \text{ mA}$	1.25	1.7	2.25	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 50 \text{ V}; I_{D} = 20 \text{ mA}$	8.0	1.3	1.8	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	-	2.8	μΑ
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	77	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	280	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 16.66 \text{ A}$	-	0.07	-	Ω
C <sub>rs</sub>	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	5.5	-	pF
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	414	-	pF
C <sub>oss</sub>	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	184	-	pF

### 6.2 RF characteristics

#### Table 7. RF characteristics

Mode of operation: pulsed RF;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %; f = 225 MHz; RF performance at  $V_{DS}$  = 50 V;  $I_{Dg}$  = 40 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Dy	) Casc )					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L</sub> = 1400 W	<tbd></tbd>	23	<tbd></tbd>	dB
RLin	input return loss	P <sub>L</sub> = 1400 W	<tbd></tbd>	-17	-	dB
$\eta_{D}$	drain efficiency	$P_L = 1400 \text{ W}$	<tbd></tbd>	69	-	%



### 6.3 Ruggedness in class-AB operation

The BLF578XR and BLF578XRS are capable of withstanding a load mismatch corresponding to VSWR > 65 : 1 through all phases under the following conditions:  $V_{DS} = 50 \text{ V}$ ;  $I_{Dq} = 40 \text{ mA}$ ;  $P_L = 1400 \text{ W}$  pulsed; f = 225 MHz.

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### 7. Package outline

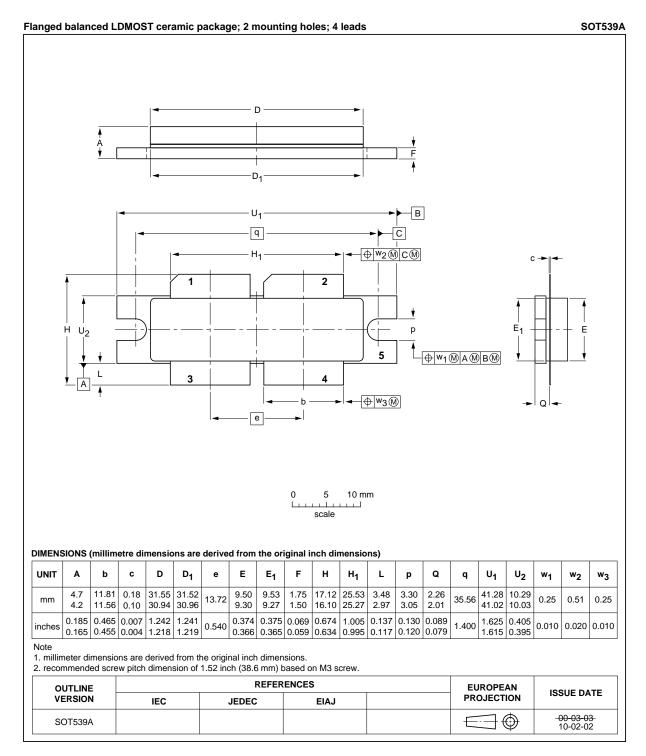


Fig 3. Package outline SOT539A

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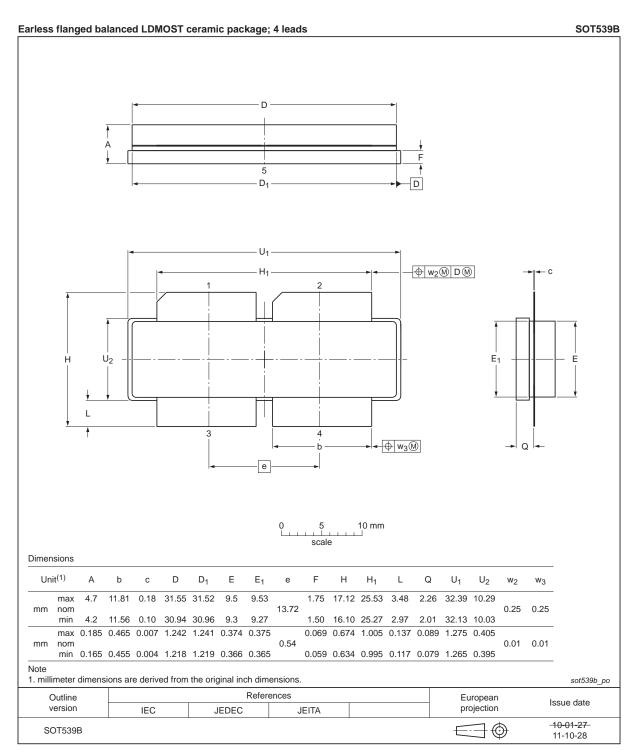


Fig 4. Package outline SOT539B

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### 8. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 9. Abbreviations

Table 8. Abbreviations

Acronym	Description
CW	Continuous Wave
DC	Direct Current
ESD	ElectroStatic Discharge
HF	High Frequency
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor
RF	Radio Frequency
VSWR	Voltage Standing-Wave Ratio
XR	eXtremely Rugged

### 10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF578XR_BLF578XRS v.1	20120130	Objective data sheet	-	-

### 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Date of release: 30 January 2012
Document identifier: BLF578XR\_BLF578XRS